

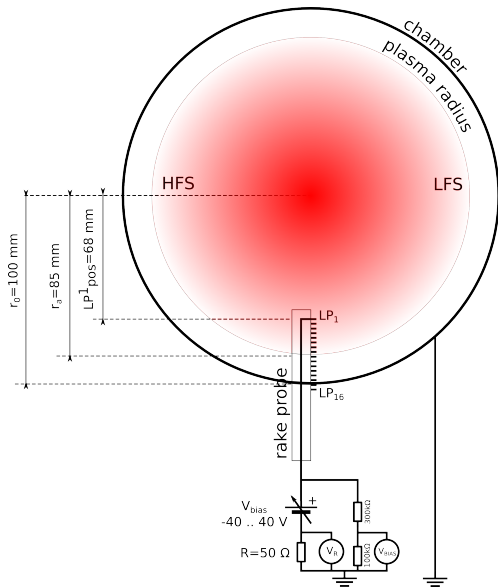
# VA characteristics @GOLEM

Vojtech Svoboda Jan Stockel

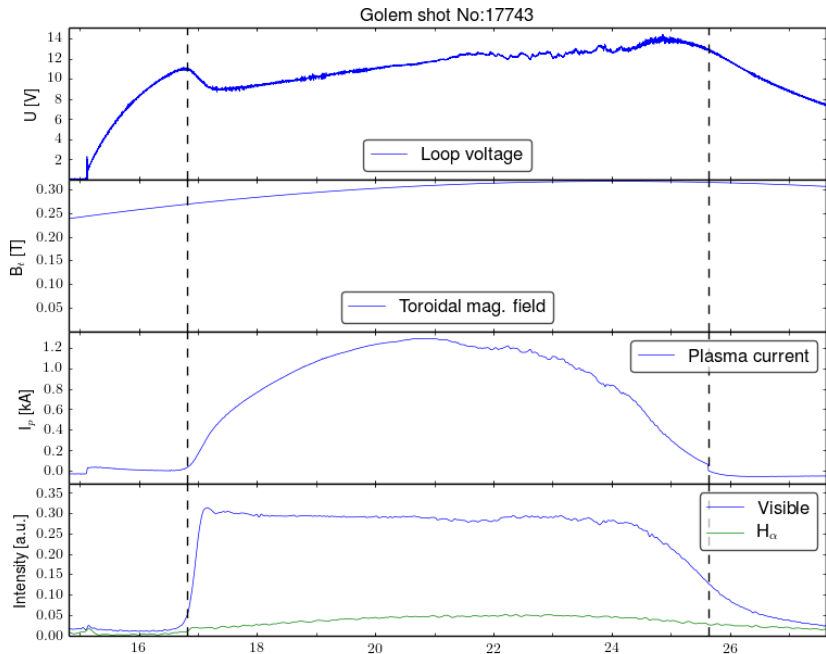
FNSPE CTU Prague

2015

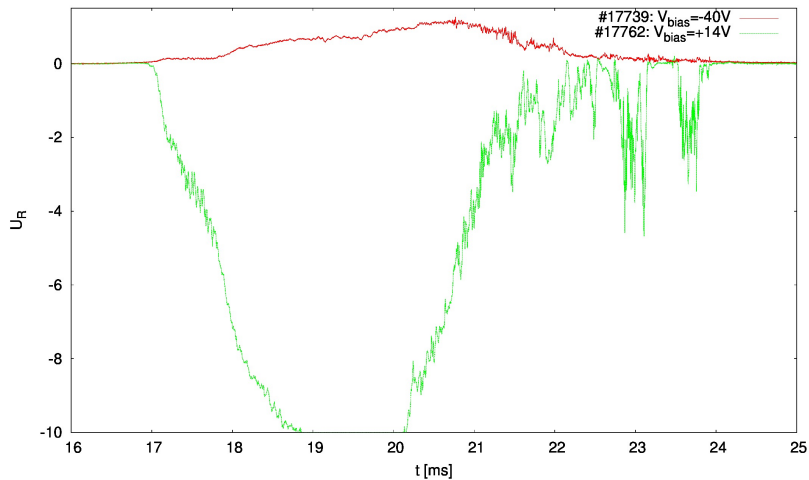
# Experimental setup



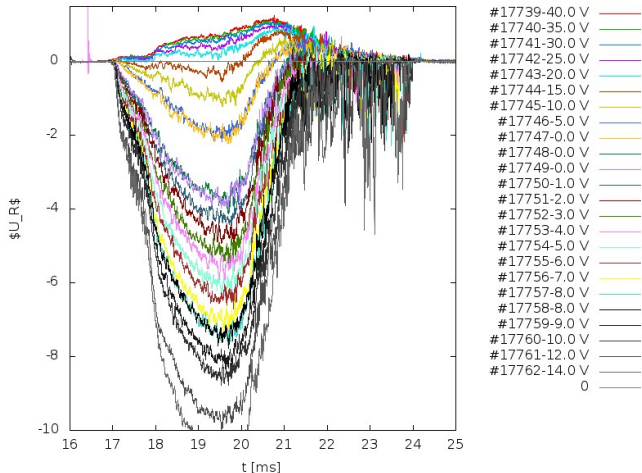
# Reference discharge #17743



# Raw signals: electron & ion signal

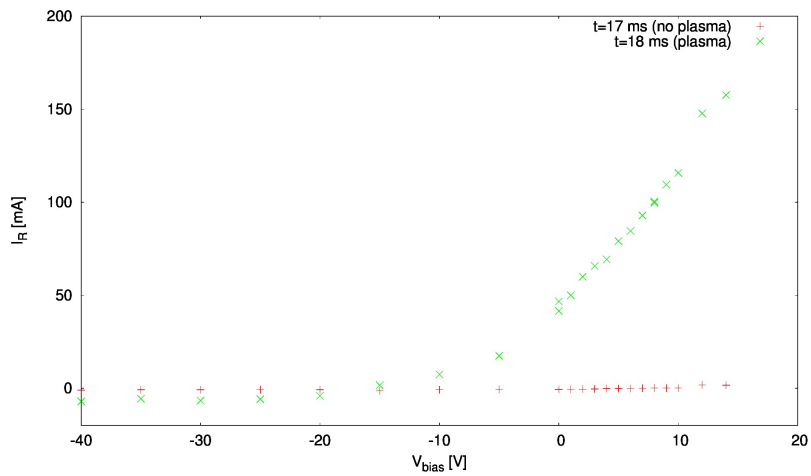


# Raw signals altogether

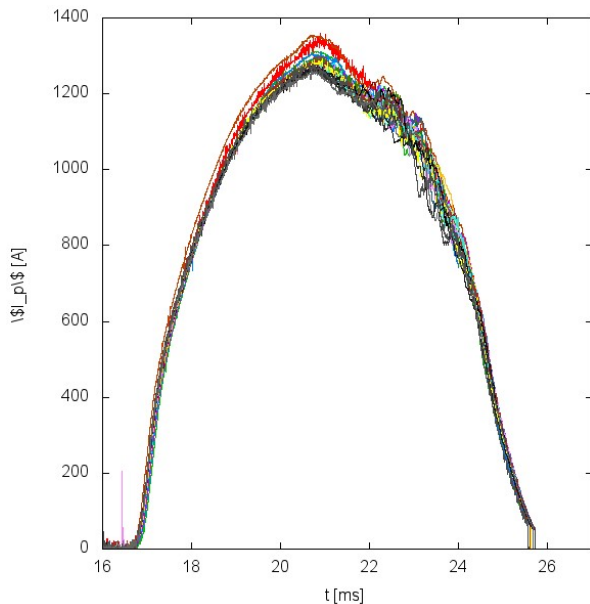


Let's make cut @17ms & @18ms →

# VA characteristics



# Discharge reproducibility @GOLEM



- #17739-40.0 V
- #17740-35.0 V
- #17741-30.0 V
- #17742-25.0 V
- #17743-20.0 V
- #17744-15.0 V
- #17745-10.0 V
- #17746-5.0 V
- #17747-0.0 V
- #17748-0.0 V
- #17749-0.0 V
- #17750-1.0 V
- #17751-2.0 V
- #17752-3.0 V
- #17753-4.0 V
- #17754-5.0 V
- #17755-6.0 V
- #17756-7.0 V
- #17757-8.0 V
- #17758-8.0 V
- #17759-9.0 V
- #17760-10.0 V
- #17761-12.0 V
- #17762-14.0 V
- 0

# LP theory - use 3 parameter fit

## How to extract plasma parameters

The knee of the I-V characteristics identifies the plasma potential  $V_{pl}$ .

$V_f$ : the “floating potential”  $\rightarrow$  no current driven to the probe.

Plasma potential:  $V_{pl} = V_f + \Delta T_e$

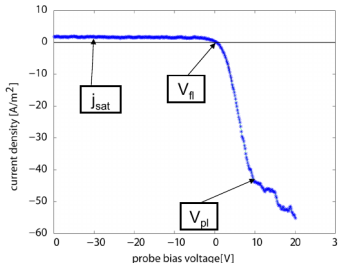
$I_{sat}$ : ion saturation current. Often we work directly with  $J_{sat} = I_{sat}/A_s$ , with  $A_s$  the particle collection area – this is identified with  $A_p$ , the projected area when  $B \neq 0$  (see later).

Once  $I_{sat}$  and  $T_e$  are known, the density at the sheath edge follows:

$$n_{se} = I_{sat}/Z_i e c_s A_s$$

However, the knee is not well defined (see practicum III).

Usual way to extract information from LP characteristic is to use a 3 parameter non-linear least square fit to obtain  $I_{sat}$ ,  $V_f$  and  $T_e$ .



$$I = I_{sat} \left[ 1 - \exp \left( - \frac{V - V_{fl}}{T_e} \right) \right]$$





# LP theory - empirical parametrization

$$I(a, V_{bias}) = \exp[a_1 \tanh(V_{bias} + a_2)/a_3] + a_4$$

103501-5 Parameterization of Langmuir probe data

Rev. Sci. Instrum. 79, 103501 (2008)

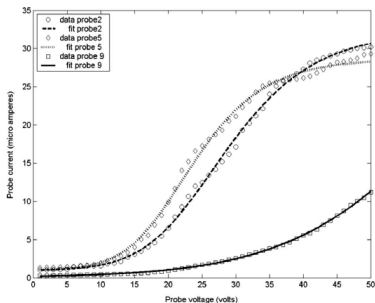


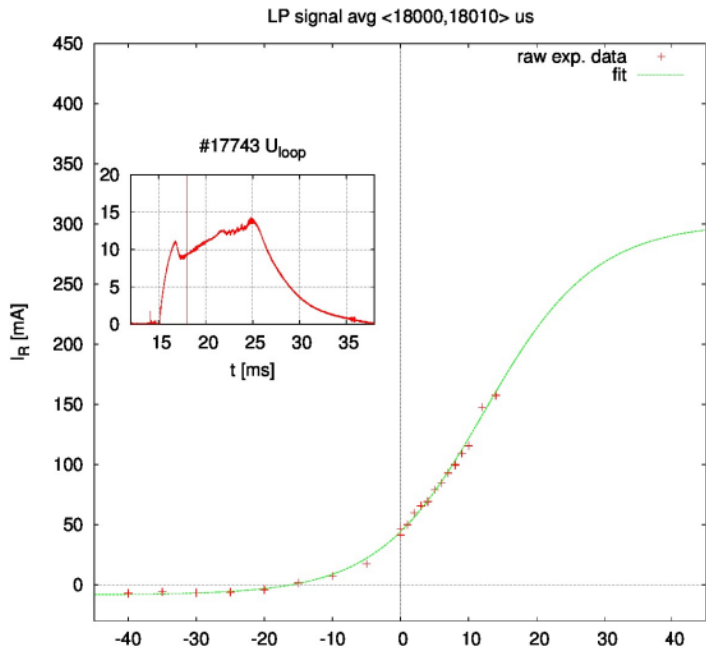
FIG. 8. Experimental and fitted  $I$ - $V$  characteristics for three probes.

are much similar to probes 2 and 5. The current scale of probe 9 is lower than those obtained for other probes. This probe is very close to the glass discharge vessel where wall effects are dominant. Evaluation of the second differential  $d^2I/dV^2$ , plasma potential  $V_p$ , the EEDF, and thus the plasma electron temperature  $T_e$  are carried out using both the fitting method and ac differentiating signal data. Typical plot of  $d^2I/dV^2$  and the EEDF using both methods for one of the probes are shown in Fig. 9.

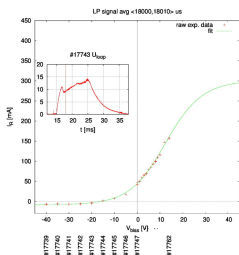
It can be said that there is an acceptable agreement between values of the plasma potential and the general shape of the EEDF obtained using the two methods. Part of the discrepancies between the two may be associated with some of the limitations associated with ac differentiation. One of these limitations is connected to the experimental difficulty of measuring very small differences in probe current for the ac on and ac off cases. This is particularly true at higher probe dc probe biases that correspond to the higher electron energy tail of the EEDF. A second limitation associated with ac differentiation is the effect of instrument convolution

Azzoz@RevSciInst(2008) + code@matlab

# Empirical parametrization on the GOLEM data



# Extracted parameters



- ▶ Ion saturation current:  
 $I_{is} = I(a, 2 * \min(V_{bias}))$
- ▶ Electron saturation current:  
 $I_{es} = I(a, 3 * \max(V_{bias}))$
- ▶ Plasma potential:  
 $V_p = a_3 * \operatorname{atanh}(((\sqrt{1 + a_1^2}) - 1)/a_1) - a_2;$
- ▶ Floating potential  $V_{fl}$  from the condition  
 $I(a, V_{fl}) = 0$

- ▶ Electron energy distribution function (EEDF):  $N(\epsilon) = \frac{2}{Ae} \sqrt{\frac{2m\epsilon}{e}} \frac{d^2I}{dV^2}$
- ▶ Electron energy distribution function (EEDF):  $P(\epsilon) = \frac{2}{Ae} \sqrt{\frac{2m}{e}} \frac{d^2I}{dV^2}$
- ▶ Electron density

$$n_e = \int_0^{\infty} P(\epsilon) d\epsilon$$

- ▶ Ion density  $n_i = \frac{|I_{is}|}{0.52 * A * e^{2/3}} \sqrt{\frac{M_i}{T_e}}$
- ▶ Electron temperature

$$T_e = \frac{2}{3} \langle \epsilon \rangle = \frac{2}{3n_e} \int_0^{\infty} \epsilon P(\epsilon) d\epsilon$$

## Harmonic method for EEDF measurements

$$\frac{d^2 I_e}{dV^2} = \frac{2\pi e^3}{m_e^2} A_p f[v(\varepsilon)]$$

$$\varepsilon = \frac{1}{2} m v^2$$

$$F(\varepsilon) d\varepsilon = 4\pi v^2 f(v) dv$$

$$f(v) = \frac{m_e^2}{2\pi e^3 A_p} \frac{d^2 I_e}{dV^2}$$

Druyvesteyn formula

$$F(\varepsilon) = \frac{4}{e^2 A_p} \sqrt{\frac{mV}{2e}} \frac{d^2 I_e}{dV^2}$$

Practically, a modulation  $\delta(t)$  is superposed on the biasing voltage and the second harmonic component is measured which is proportional to the EEDF.

$$I(V) = I[V_0 + \delta(t)] = I(V_0) + \delta(t) \frac{dI(V_0)}{dV} + \frac{1}{2} [\delta(t)]^2 \frac{d^2 I(V_0)}{dV^2} + \dots$$



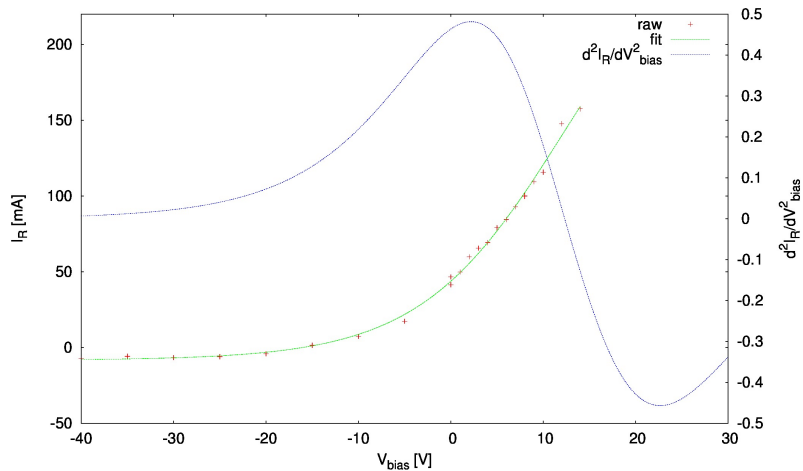
M. Druyvesteyn and F. Penning, *Reviews of Modern Physics*, vol. 12, no. 2, 87, (1940).

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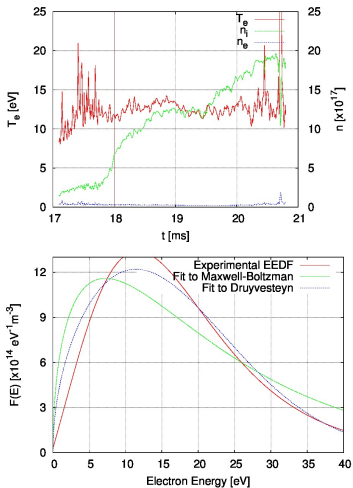
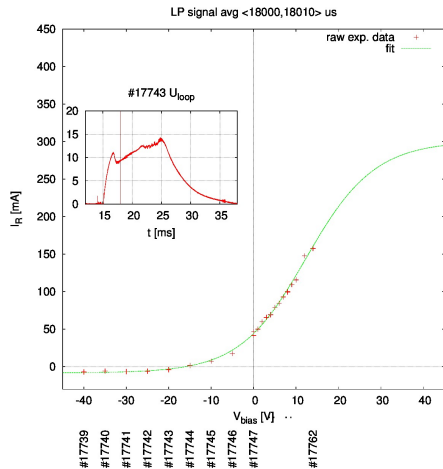


Furno et al.: Theory of electrostatic probes

# The second derivative of VA characteristics

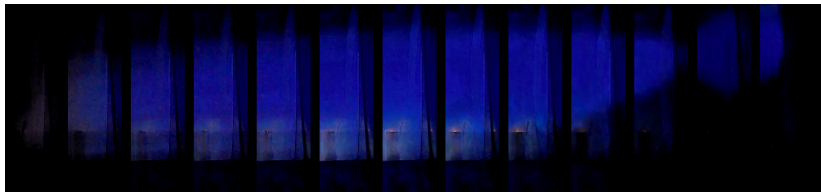


# Final video frame



<https://www.youtube.com/watch?v=yd54Cy2tFT4>

# Signal vanish



# Summary

- ▶ VA characteristic measured on the shot to shot base
- ▶ unique data obtained